

WEST Search History for Application 10520456

Creation Date: 2009042015:59

Query	DB	Op.	Plur.	Thes.	Date
gordon-\$.in. or suh-\$.in. or becker-\$.in.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(gordon-\$.in. or suh-\$.in. or becker-\$.in.) and vapor deposition	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(vapor deposition same (tungstein or molybdenum or W or Mo))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((vapor deposition same (tungstein or molybdenum or W or Mo))) and (gordon-\$.in. or suh-\$.in. or becker-\$.in.)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(vapor deposition same (tungstein or molybdenum or W or Mo) same nitride)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((vapor deposition same (tungstein or molybdenum or W or Mo) same nitride)) and (gordon-\$.in. or suh-\$.in. or becker-\$.in.)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(vapor deposition with (tungstein or molybdenum or W or Mo) near2 nitride)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(vapor deposition with (tungstein or molybdenum or W or Mo) near nitride)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(tungstein or molybdenum or W or Mo) near nitride	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((tungstein or molybdenum or W or Mo) near	PGPB, USPT,	ADJ	YES		04-20-2009

nitride) with vapor deposition	USOC, EPAB, JPAB, DWPI, TDBD			
compound.clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((compound.clm.) and ((vapor deposition with (tungstein or molybdenum or W or Mo) near nitride))	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) with compound).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) with compound with nitride).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
vapor deposition and (((tungstein or molybdenum or W or Mo) with compound with nitride).clm.)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) near nitride).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) near nitride).clm.) and vapor deposition	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) near nitride).clm.) same vapor deposition	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) with compound with nitride).clm.) and compound	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009
((tungstein or molybdenum or W or Mo) with compound with nitride).clm.) same compound.clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES	04-20-2009

(compound with (tungstein or molybdenum or W or Mo) near nitride).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((compound with (tungstein or molybdenum or W or Mo) near nitride).clm.) and vapor deposition	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((compound with (tungstein or molybdenum or W or Mo) near nitride).clm.) and (vapor deposition).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
analogous with tungsten with molybdenum	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(analogous with tungsten with molybdenum) and vapor deposition	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(analogous with tungsten with molybdenum) with (vapor depsoition)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(analogous with tungsten with molybdenum) same (vapor depsoition)	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
(analogous with tungsten with molybdenum) same semiconductor	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((thin film near2 deposit\$) with vapor).clm.	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((((thin film near2 deposit\$) with vapor).clm.) wit hadsor\$	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009
((((thin film near2 deposit\$) with vapor).clm.) with adsor\$	PGPB, USPT, USOC, EPAB, JPAB, DWPI, TDBD	ADJ	YES		04-20-2009